







**Fexas** Instruments

SN74AUC1GU04

SCES371M-SEPTEMBER 2001-REVISED JUNE 2017

# SN74AUC1GU04 Single Inverter Gate

#### Features 1

- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
  - 2000-V Human-Body Model (A114-A)
  - 200-V Machine Model (A115-A)
  - 1000-V Charged-Device Model (C101)
- Available in the Texas Instruments NanoFree<sup>™</sup> Package
- Optimized for 1.8-V Operation and Is 3.6-V I/O Tolerant to Support Mixed-Mode Signal Operation
- Sub-1-V Operable
- Max t<sub>pd</sub> of 2.4 ns at 1.8 V
- Low Power Consumption, 10-µA Max I<sub>CC</sub>
- ±8-mA Output Drive at 1.8 V
- **Unbuffered Output**
- Ioff Supports Partial Power Down Mode and Back **Drive Protection**

#### Applications 2

- **AV Receiver**
- Audio Dock: Portable
- Blu-Ray Player and Home Theater
- Embedded PC
- MP3 Player/Recorder (Portable Audio)
- Personal Digital Assistant (PDA)
- Power: Telecom/Server AC/DC Supply: Single Controller: Analog and Digital
- Solid State Drive (SSD): Client and Enterprise
- TV: LCD/Digital and High-Definition (HDTV) •
- **Tablet: Enterprise**
- Video Analytics: Server ٠
- Wireless Headset, Keyboard, and Mouse

# 3 Description

This single inverter gate is operational at 0.8-V to 2.7-V V<sub>CC</sub>, but is designed specifically for 1.65-V to 1.95- $V V_{CC}$  operation.

The SN74AUC1GU04 device contains one inverter with an unbuffered output and performs the Boolean function Y = A.

NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

Device information."										
PART NUMBER	PACKAGE	BODY SIZE (NOM)								
SN74AUC1GU04DBV	SOT-23 (5)	2.90 mm × 1.60 mm								
SN74AUC1GU04DCK	SC70 (5)	2.00 mm × 1.25 mm								
SN74AUC1GU04YZP	DSBGA (5)	1.75 mm × 1.25 mm								

(1) For all available packages, see the orderable addendum at the end of the data sheet.

## Logic Diagram (Positive Logic)



## vice Information<sup>(1)</sup>

STRUMENTS

XAS

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## 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision	L (April 2007) to Revision M
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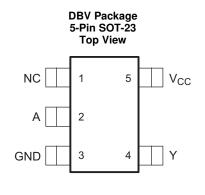
Page

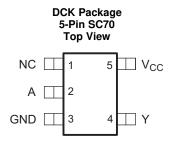
•	Deleted DRY package throughout data sheet	1
•	Added Applications, Device Information table, Pin Configuration and Functions section, ESD Ratings table, Thermal	
	Information table, Feature Description section, Device Functional Modes, Device and Documentation Support	
	section, and Mechanical, Packaging, and Orderable Information section	1

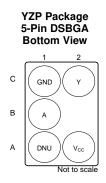
• Deleted Ordering Information table, see Mechanical, Packaging, and Orderable Information at the end of the data sheet. 1



# 5 Pin Configuration and Functions







See mechanical drawings for dimensions.

NC - No internal connection

DNU - Do not use

#### **Pin Functions**

PIN		I/O	DESCRIPTION						
NAME	DBV, DCK	YZP	1/0	DESCRIPTION					
А	2	B1	I	A logic input					
DNU	—	A1	—	Do not use					
GND	3	C1	—	Ground					
NC	1	_	—	No internal connection					
V <sub>CC</sub>	5	A2	—	Positive supply					
Υ	4	C2	0	Y unbuffered inverted output					

## 6 Specifications

## 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

				MIN	MAX	UNIT
$V_{CC}$	Supply voltage			-0.5	3.6	V
VI	Input voltage <sup>(2)</sup>				3.6	V
Vo	Output voltage <sup>(2)</sup>	Output voltage <sup>(2)</sup>		-0.5	$V_{CC} + 0.5$	V
I <sub>IK</sub>	Input clamp current	V <sub>1</sub> < 0			-50	mA
I <sub>OK</sub>	Output clamp current	V <sub>O</sub> < 0			-50	mA
I <sub>O</sub>	Continuous output current				±20	mA
	Continuous current through V <sub>CC</sub> or GND	Continuous current through V <sub>CC</sub> or GND			±100	mA
T <sub>stg</sub>	Storage temperature			-65	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

## 6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	2000	
	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 $^{\left( 2\right) }$	1000	V
		Machine Model (A115-A)		

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

## 6.3 Recommended Operating Conditions

#### See<sup>(1)</sup>

			MIN	МАХ	UNIT
$V_{CC}$	Supply voltage		0.8	2.7	V
V <sub>IH</sub>	High-level input voltage	I <sub>O</sub> = −100 μA	$0.65 \times V_{CC}$		V
$V_{\text{IL}}$	Low-level input voltage	I <sub>O</sub> = 100 μA		$0.35 \times V_{CC}$	V
VI	Input voltage		0	3.6	V
Vo	Output voltage		0	V <sub>CC</sub>	V
		$V_{CC} = 0.8 V$		-0.7	
I <sub>OH</sub>		$V_{CC} = 1.1 V$		-3	
I <sub>OH</sub>	High-level output current	$V_{CC} = 1.4 V$		-5	mA
		$V_{CC} = 1.65 V$		-8	
		$V_{CC} = 2.3 V$		-9	
		$V_{CC} = 0.8 V$		0.7	
		$V_{CC} = 1.1 V$		3	
I <sub>OL</sub>	Low-level output current	$V_{CC} = 1.4 V$		5	mA
		$V_{CC} = 1.65 V$		8	
		$V_{CC} = 2.3 V$		9	
$\Delta t / \Delta v$	Input transition rise or fall rate			20	ns/V
T <sub>A</sub>	Operating free-air temperature		-40	85	°C

 All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. See *Implications of Slow or Floating* CMOS Inputs, SCBA004.



#### 6.4 Thermal Information

	THERMAL METRIC <sup>(1)</sup>	DBV (SOT-23)	DCK (SC70)	YZP (DSBGA)	UNIT
		5 PINS	5 PINS	5 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	206	252	132	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

## 6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V <sub>cc</sub>	MIN TYP <sup>(1)</sup> MAX	UNIT	
	$I_{OH} = -100 \ \mu A$	0.8 V to 2.7 V	V <sub>CC</sub> – 0.1		
	0.55				
	0.8	.,			
VOH	$I_{OH} = -5 \text{ mA}$	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	V		
	$I_{OH} = -8 \text{ mA}$	1.65 V	1.2		
	$I_{OH} = -9 \text{ mA}$	2.3 V	1.8		
$V_{OH} = \frac{I_{OH} = -100 \ \mu A}{I_{OH} = -0.7 \ m A} = \frac{0.8 \ V \ to 2.7 \ V}{0.8 \ V \ to 2.7 \ V} = \frac{V_{CC} - 0.1}{V_{CC} - 0.1} = \frac{100 \ \mu A}{I_{OH} = -0.7 \ m A} = \frac{0.8 \ V}{0.8 \ V} = \frac{1.1 \ V}{0.8 \ V} = \frac{1.1 \ V}{0.8 \ V} = \frac{1.1 \ V}{1.1 \ V} = 1$	I <sub>OL</sub> = 100 μA	0.8 V to 2.7 V	0.2		
	0.25				
N	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	V			
VOL	$I_{OL} = 5 \text{ mA}$	1.4 V	0.4	v	
	I <sub>OL</sub> = 8 mA	1.65 V	0.45		
	I <sub>OL</sub> = 9 mA	2.3 V	0.6	1	
II A input	V <sub>I</sub> = V <sub>CC</sub> or GND	0 to 2.7 V	±5	μA	
I <sub>CC</sub>	$V_{I} = V_{CC}$ or GND, $I_{O} = 0$	0.8 V to 2.7 V	10	μA	
	V <sub>I</sub> = V <sub>CC</sub> or GND	2.5 V	3	pF	

(1) All typical values are at  $T_A = 25^{\circ}C$ .



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## 6.6 Switching Characteristics: C<sub>L</sub> = 15 pF

over recommended operating free-air temperature range,  $C_L = 15 \text{ pF}$  (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = 0.8 V	8 V V <sub>CC</sub> = 1.2 V ± 0.1 V		V <sub>CC</sub> = 1.5 V ± 0.1 V		V <sub>CC</sub> = 1.8 V ± 0.15 V			V <sub>CC</sub> = 2.5 V ± 0.2 V		UNIT
			ТҮР	MIN	MAX	MIN	MAX	MIN	ТҮР	MAX	MIN	MAX	
t <sub>pd</sub>	А	Y	1.9	0.6	2.5	0.6	1.7	0.3	1.1	2.3	0.2	2	ns

## 6.7 Switching Characteristics: $C_L = 30 \text{ pF}$

over recommended operating free-air temperature range,  $C_L = 30 \text{ pF}$  (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)		<sub>C</sub> = 1.8 \ : 0.15 V	/	V <sub>CC</sub> = 2.5 V ± 0.2 V		UNIT
	(INPOT)	(001901)	MIN	ТҮР	MAX	MIN	MAX	
t <sub>pd</sub>	А	Y	0.6	1.1	2.4	0.5	2.1	ns

## 6.8 **Operating Characteristics**

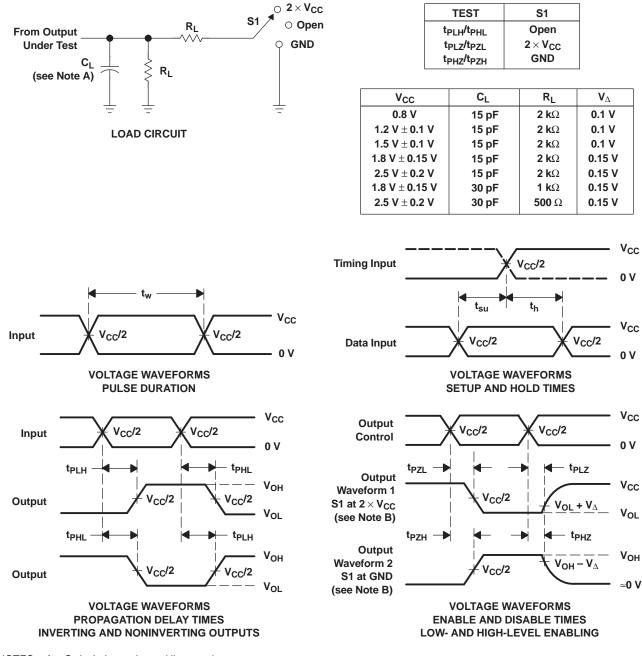
 $T_A = 25^{\circ}C$ 

	PARAMETER	TEST CONDITIONS	V <sub>CC</sub> = 0.8 V TYP	V <sub>CC</sub> = 1.2 V TYP	V <sub>CC</sub> = 1.5 V TYP	V <sub>CC</sub> = 1.8 V TYP	V <sub>CC</sub> = 2.5 V TYP	UNIT
C <sub>pd</sub>	Power dissipation capacitance	f = 10 MHz	4	4	4	4	5	pF

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### 7 Parameter Measurement Information



- NOTES: A. C<sub>L</sub> includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
  - C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz, Z<sub>O</sub> = 50  $\Omega$ , slew rate  $\geq$  1 V/ns.
  - D. The outputs are measured one at a time, with one transition per measurement.
  - E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
  - F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
  - G. t<sub>PLH</sub> and t<sub>PHL</sub> are the same as t<sub>pd</sub>.
  - H. All parameters and waveforms are not applicable to all devices.

### Figure 1. Load Circuit and Voltage Waveforms

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## 8 Detailed Description

## 8.1 Functional Block Diagram

A \_\_\_\_\_ Y

Figure 2. Logic Diagram (Positive Logic)

## 8.2 Device Functional Modes

Table 1 lists the functional modes of the SN74AUC1GU04.

## Table 1. Function Table

INPUT A	OUTPUT Y
Н	L
L	н



## 9 Device and Documentation Support

## 9.1 Documentation Support

#### 9.1.1 Related Documentation

For related documentation see the following:

Implications of Slow or Floating CMOS Inputs, SCBA004

### 9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

## 9.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E<sup>™</sup> Online Community *TI's Engineer-to-Engineer (E2E) Community.* Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

## 9.4 Trademarks

NanoFree, E2E are trademarks of Texas Instruments. All other trademarks are the property of their respective owners.

### 9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 9.6 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

## 10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



10-Dec-2020

## PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
SN74AUC1GU04DBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	UU4R	Samples
SN74AUC1GU04DCKR	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	UDR	Samples
SN74AUC1GU04YZPR	ACTIVE	DSBGA	YZP	5	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	UDN	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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# PACKAGE OPTION ADDENDUM

10-Dec-2020

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

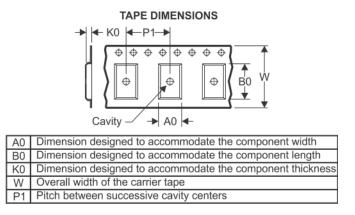
# **PACKAGE MATERIALS INFORMATION**

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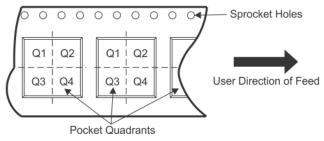
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## **TAPE AND REEL INFORMATION**





## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



All dimensions are nominal        Device      Package      Package      Pins      SPQ      Reel      A0      B0      K0      P1      W      Pin1												
	Туре	Drawing			Diameter (mm)	Width W1 (mm)	(mm)	(mm)	(mm)	(mm)	(mm)	Quadrant
SN74AUC1GU04DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74AUC1GU04DCKR	SC70	DCK	5	3000	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
SN74AUC1GU04YZPR	DSBGA	YZP	5	3000	178.0	9.2	1.02	1.52	0.63	4.0	8.0	Q1

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# PACKAGE MATERIALS INFORMATION

18-Jan-2020



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74AUC1GU04DBVR	SOT-23	DBV	5	3000	202.0	201.0	28.0
SN74AUC1GU04DCKR	SC70	DCK	5	3000	202.0	201.0	28.0
SN74AUC1GU04YZPR	DSBGA	YZP	5	3000	220.0	220.0	35.0

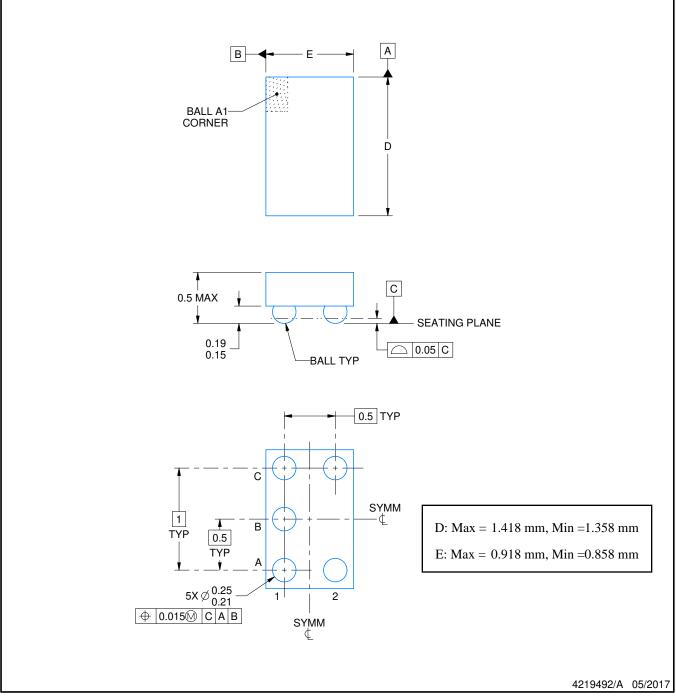
# **YZP0005**



# **PACKAGE OUTLINE**

# DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice.

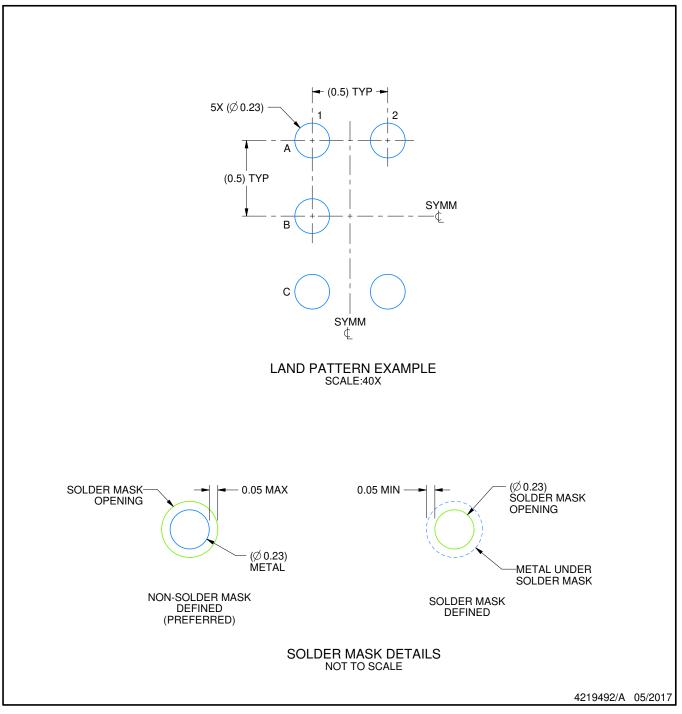


# YZP0005

# **EXAMPLE BOARD LAYOUT**

# DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).

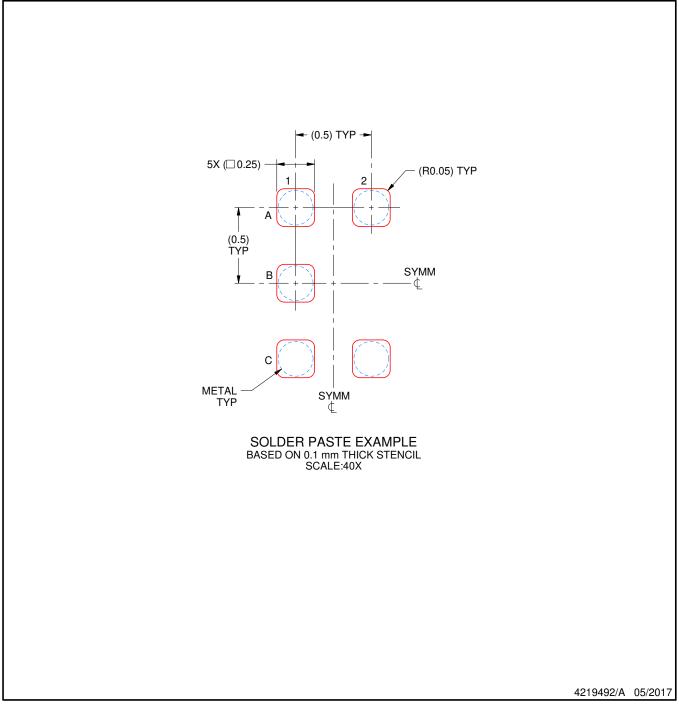


# YZP0005

# **EXAMPLE STENCIL DESIGN**

# DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



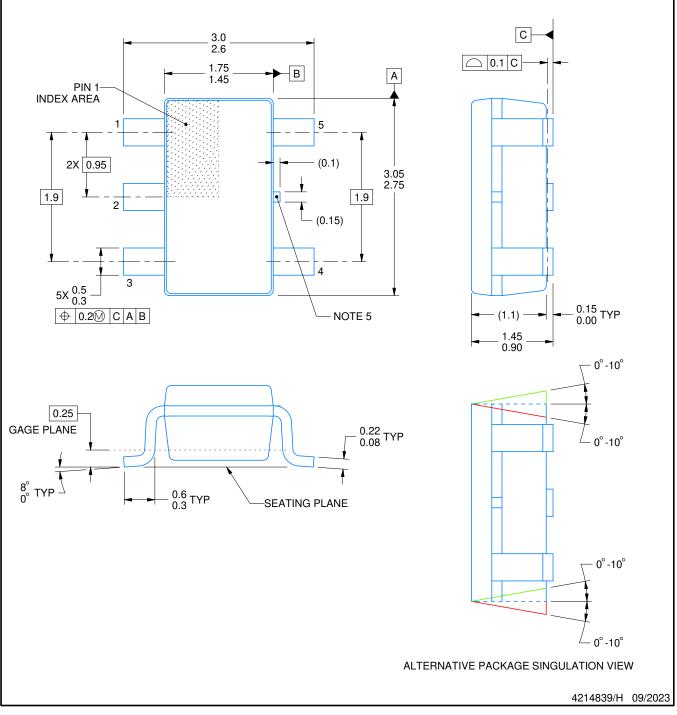
# **DBV0005A**



# **PACKAGE OUTLINE**

# SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.This drawing is subject to change without notice.Refernce JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
- 5. Support pin may differ or may not be present.

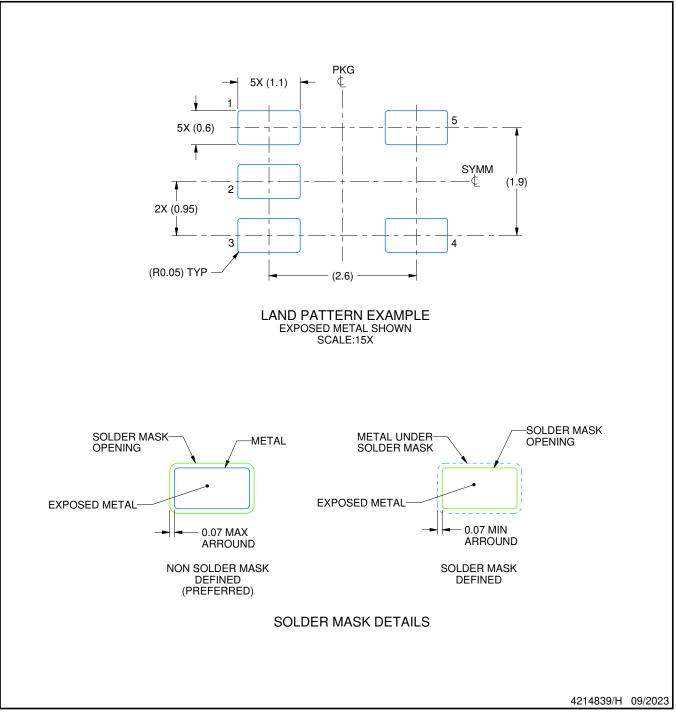


# **DBV0005A**

# **EXAMPLE BOARD LAYOUT**

# SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

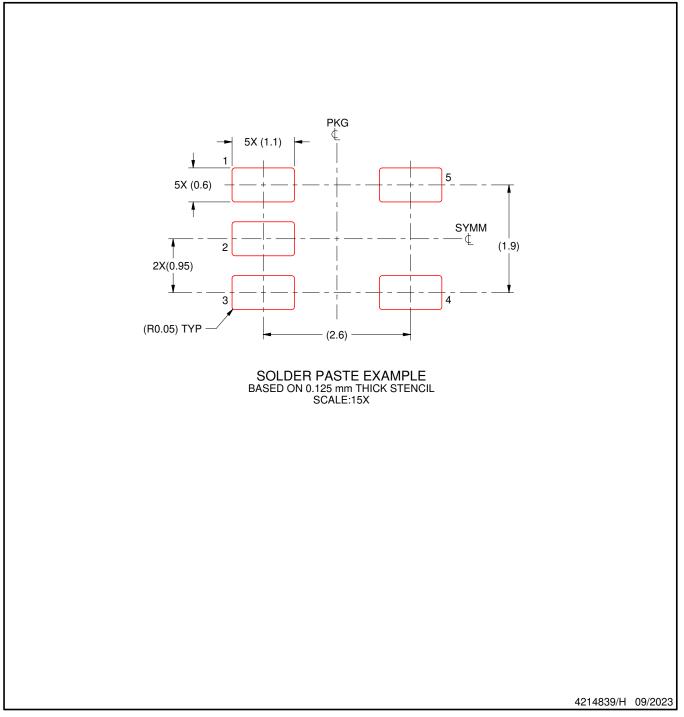


# **DBV0005A**

# **EXAMPLE STENCIL DESIGN**

# SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



# DCK0005A



# **PACKAGE OUTLINE**

# SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
  This drawing is subject to change without notice.
  Reference JEDEC MO-203.
  Support pin may differ or may not be present.



# **DCK0005A**

# **EXAMPLE BOARD LAYOUT**

# SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

4. Publication IPC-7351 may have alternate designs.5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



# DCK0005A

# **EXAMPLE STENCIL DESIGN**

# SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)



<sup>6.</sup> Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

<sup>7.</sup> Board assembly site may have different recommendations for stencil design.

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